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(54) **GATE-ALL-AROUND TRANSISTORS WITH  
CLADDED SOURCE/DRAIN REGIONS**

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(71) Applicant: **International Business Machines  
Corporation**, Armonk, NY (US)

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(72) Inventors: **Julien Frougier**, Albany, NY (US);  
**Ruilong Xie**, Niskayuna, NY (US);  
**Andrew M. Greene**, Slingerlands, NY  
(US); **Curtis S. Durfee**, Schenectady,  
NY (US); **Oleg Gluschenkov**,  
Tannersville, NY (US); **Andrew Gaul**,  
Halfmoon, NY (US)

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(57) **ABSTRACT**

A semiconductor structure includes a gate region, a source/  
drain region, and a nanosheet semiconductor layer extending  
continuously across the gate region and the source/drain  
region. The nanosheet semiconductor layer includes a first  
portion in the gate region and a second portion in the  
source/drain region. The source/drain region includes a  
cladded epitaxial layer wrapping around the second portion  
of the nanosheet semiconductor layer.

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